

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	17	(("6677192") or ("6723661") or ("6717216") or ("6707106") or ("6646322") or ("20040113217") or ("20040113174") or ("20040026736") or ("20030102490") or ("20030094637") or ("20030027393") or ("20020109135") or ("20030219937") or ("20020179946") or ("20040061172") or ("6674100") or ("6630710")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/04 18:05
S1	25597	soi	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:04
S2	256	sgoi	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:08
S3	1250	goi	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:04
S4	9651	sige	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:04
S5	37	S3 and S4	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:04
S6	66	silicon adj germanium and S3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:07
S7	315	(silicon adj germanium or S4) and (S2 or S3)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:05

S8	1594	sgoi or SiGe-On-Insulator or Ge-On-Insulator or goi	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:09
S9	98	S8 not S2 not S3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:09
S10	5675	silicon with (strained straining strain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:07
S11	253	S8 and S10	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:11
S12	157	S11 and source and channel and drain	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:19
S13	121	S12 and (polysilic\$5 or polycrystal\$5)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:24
S14	0	S12 and (polysilic\$5 or polycrystal\$5) not (polysilicon or polycrystal or polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:24
S15	121	S12 and (polysilicon or polycrystal or polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 15:26
S16	23	S12 and (polysilicon or polycrystal or polycrystalline) with (source or drain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2005/12/04 16:04
S17	9190	(poly-si polysilicon or polycrystal or polycrystalline) near3 (source or drain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2005/12/04 16:05

S18	1686	(poly-si polysilicon or polycrystal or polycrystalline) near (source or drain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2005/12/04 16:30
S19	5886	silicon with (strained straining strain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2005/12/04 16:07
S20	739774	(ge or germanium or sige)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:08
S21	11	S18 and S19 and S20	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:37
S23	29924	(poly-si polysilicon or polycrystal or polycrystalline) with (source or drain)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2005/12/04 16:37
S26	201	S23 and S19 and S20 not S21	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 17:42
S27	2958	(257/18,19,347,353).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/04 17:42